140 COMMERCE DRIVE
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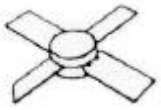
MS2206

RF & MICROWAVE TRANSISTORS
AVIONICS APPLICATIONS



.280 4LSL (M115)
Epoxy Sealed

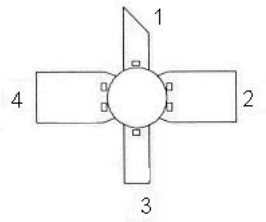
Features

- 1025-1150 MHz
- GOLD METALLIZATION
- INFINITE VSWR CAPABILITY @ RATED CONDITIONS
- Pout = 4 W MINIMUM
- G_P= 10 dB
- COMMON BASE CONFIGURATION

DESCRIPTION:

The MS2206 is a common base, silicon NPN microwave transistor designed for Class C driver applications under DME or IFF pulse conditions. This device is capable of withstanding an infinite load VSWR at any phase angle under rated conditions.

PIN CONNECTION



1. COLLECTOR
2. BASE
3. EMITTER
4. BASE

ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit
P_{DISS}	Power Dissipation	7.5	W
V_{CE}	Collector-Emitter Bias Voltage	37	V
T_J	Junction Temperature	200	°C
I_C	Device Current	1.0	A
T_{STG}	Storage Temperature	-65 to +200	°C

Thermal Data

$R_{TH(J-C)}$	Junction-case Thermal Resistance*	35	°C/W

ELECTRICAL SPECIFICATIONS (Tcase = 25°C)

STATIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV_{CBO}	I_C = 1 mA	I_E = 0 mA	45	---	---	V
BV_{CEO}	I_C = 5 mA	I_B = 0mA	20	---	---	V
BV_{EBO}	I_E = 1.0 mA	I_C = 0 mA	3.5	---	---	V
I_{CES}	V_{CE} = 35 V		---	---	1.0	mA
HFE	V_{CE} = 5 V	I_C = 100 mA	20	---	120	---

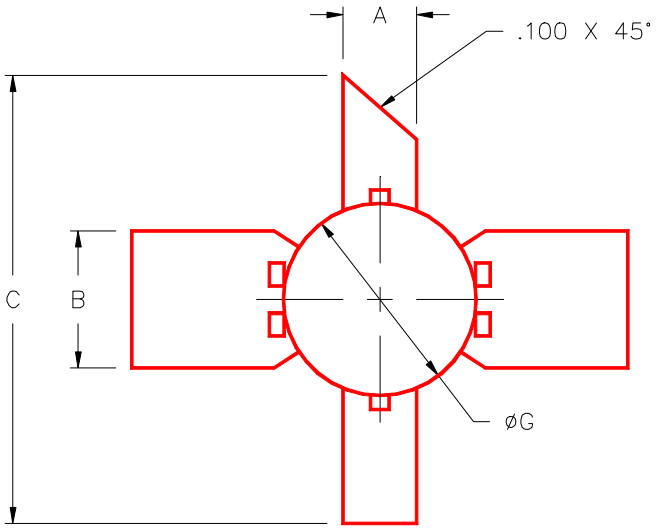
DYNAMIC

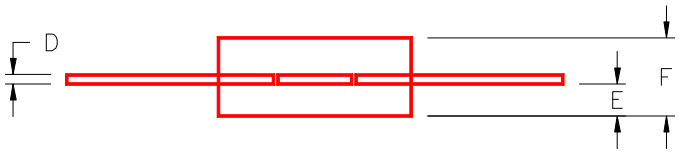
Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P_{OUT}	f =1025 - 1150 MHz	P_{IN} = 400mW	V_{CE} =35V	4	---	---	W
G_P	f =1025 - 1150 MHz	P_{IN} = 400mW	V_{CE} =35V	10	---	---	dB

Conditions: Pulse Width = 10 µs Duty Cycle = 1%

PACKAGE MECHANICAL DATA

PACKAGE STYLE M115





	MINIMUM INCHES/MM	MAXIMUM INCHES/MM		MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.095/2,41	.105/2,67			
B	.195/4,95	.205/5,21			
C	1.000/25,40				
D	.004/0,10	.007/0,18			
E	.050/1,27	.065/1,65			
F	.120/3,05	.135/3,43			
G	.275/6,99	.285/7,21			